



ELD-1450-525

- INFRARED Light Emitting Diode
- 1450 nm, 1.8 mW
- InGaAs/InP, MQW structure
- 5 mm epoxy package



Description

ELD-1450-525 is an InGaAs/InP MQW infrared LED, typically emitting at 1450 nm with an optical output power of 1.8 mW. It comes in a hermetically sealed clear 5 mm epoxy resin without standoff leads.

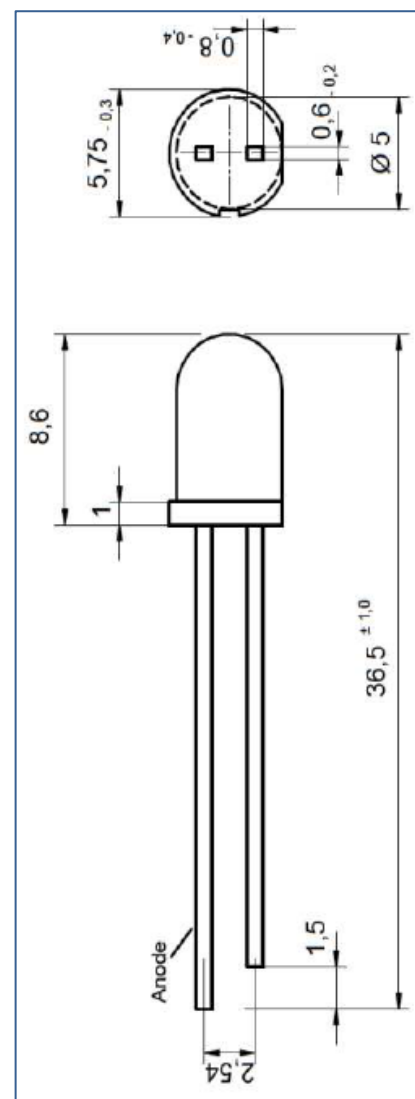
Maximum Rating ($T_{CASE} = 25^{\circ}C$)

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation, DC	P_D		100	mW
Forward Current	I_F		100	mA
Pulse Forward Current*	I_{FP}		200	mA
Operating Temperature	T_{OPR}	- 20	+ 80	$^{\circ}C$
Storage Temperature	T_{STG}	- 55	+ 100	$^{\circ}C$
Soldering Temperature (max 3s)	T_{SOL}		+ 260	$^{\circ}C$

* $t_p \leq 50 \mu s$, $t_p/T = 1/2$

Electro-Optical Characteristics ($T_{CASE} = 25^{\circ}C$, $I_F = 20 \text{ mA}$)

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Peak Wavelength	λ_P		1450		nm
Spectral Width (FWHM)	$\Delta\lambda$		150		nm
Forward Voltage @ 20 mA	V_F		0.8		V
Forward Voltage @ 100 mA	V_F		1.0		V
Reverse Voltage ($I_R = 10 \mu A$)	V_R	5			V
Radiant Power @ 20 mA	Θ_e		1.8		mW
Radiant Power @ 100 mA	Θ_e		6.5		mW
Switching time	t_R, t_F		40, 40		ns
Viewing Half Angle	$\Theta_{1/2}$		10		deg.



All dimensions in mm